NSN 5961-01-414-4330

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-414-4330 **Inclosure Material:** Ceramic **Overall Length:** 0.890 inches **Overall Height:** 0.560 inches **Overall Width:** 0.545 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-254aa **Response Time:** 35.0 nanoseconds all light emitting diode **Component Name And Quantity:** 2 semiconductor device diode **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon all light emitting diode Voltage Rating In Volts Per Characteristic: 200.0 working peak reverse voltage all light emitting diode **Current Rating Per Characteristic:** 40.00 amperes forward current, average absolute all light emitting diode and 400.00 amperes forward current, average preset all light emitting diode **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Precious Material And Location:** Plated leads gold **Precious Material:** Gold **Test Data Document:** 35351-171280 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 3 pin Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

Demilitarization: Yes - demil/mli